# VS-UFB201FA40

Vishay Semiconductors

## **Insulated Ultrafast Rectifier Module, 200 A**



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PRIMARY CHARACTERISTICS						
V <sub>R</sub>	400 V					
$I_{F(AV)}$ per module at $T_C = 86 \ ^{\circ}C$	200 A					
t <sub>rr</sub>	40 ns					
Туре	Modules - diode FRED Pt®					
Package	SOT-227					

### **FEATURES**

- Two fully independent diodes
- Fully insulated package
- Ultrafast, soft reverse recovery, with high junction temperature (T<sub>J</sub> max. = 175 °C)
- Low forward voltage drop
- Optimized for power conversion: welding and industrial SMPS applications
- Easy to use and parallel
- Industry standard outline
- UL approved file E78996
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **DESCRIPTION / APPLICATIONS**

The VS-UFB201FA40 insulated modules integrate two state of the art ultrafast recovery rectifiers in the compact, industry standard SOT-227 package. The diodes structure, and its life time control, provide an ultrasoft recovery current shape, together with the best overall performance, ruggedness and reliability characteristics.

These devices are thus intended for high frequency applications in which the switching energy is designed not to be predominant portion of the total energy, such as in the output rectification stage of welding machines, SMPS, DC/DC converters. Their extremely optimized stored charge and low recovery current reduce both over dissipation in the switching elements (and snubbers) and EMI/RFI.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Cathode to anode voltage	V <sub>R</sub>		400	V		
Continuous forward current per diode	١ <sub>F</sub>	T <sub>C</sub> = 88 °C	120	^		
Single pulse forward current per diode	I <sub>FSM</sub>	T <sub>C</sub> = 25 °C	600	A		
Maximum power dissipation per module	PD	T <sub>C</sub> = 88 °C	311	W		
RMS isolation voltage	V <sub>ISOL</sub>	Any terminal to case, t = 1 min	2500	V		
Maximum junction temperature	TJ		-55 to +175			
Maximum case temperature	T <sub>C</sub>		150	°C		
Storage temperature	T <sub>STG</sub>		-55 to +150			



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<b>ELECTRICAL SPECIFICATIONS PER DIODE</b> ( $T_J$ = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	. TEST CONDITIONS		TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	$V_{BR}$	I <sub>R</sub> = 100 μA	400	-	-		
		I <sub>F</sub> = 100 A	-	1.33	1.59		
Environd vielde en	V <sub>FM</sub>	$I_F = 100 \text{ A},  \text{T}_\text{J} = 125 \ ^\circ\text{C}$	-	1.19	1.28	V	
Forward voltage		I <sub>F</sub> = 200 A	-	1.56	1.91		
		$I_F = 200 \text{ A}, \text{ T}_J = 125 \text{ °C}$	-	1.49	1.64		
		$V_{R} = V_{R}$ rated	-	0.20	50	μA	
Reverse leakage current	I <sub>RM</sub>	$T_J = 175 \text{ °C}, V_R = V_R \text{ rated}$	$T_J = 175 \text{ °C}, V_R = V_R \text{ rated}$ - 0		2	mA	
Junction capacitance	CT	V <sub>R</sub> = 400 V	-	76	-	pF	

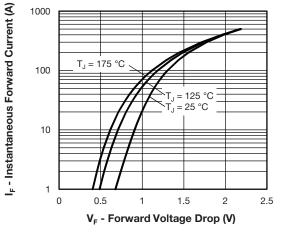
<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST C	ONDITIONS	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	40	-		
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	80	-	ns	
		T <sub>J</sub> = 125 °C		-	160	-		
Peak recovery current	1	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 50 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	7	-	А	
Peak recovery current	IRRM	T <sub>J</sub> = 125 °C		-	16	-	~	
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	310	-	nC	
		T <sub>J</sub> = 125 °C		-	1300	-		

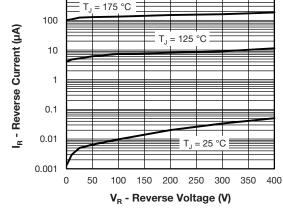
THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Junction to case, single leg conducting	Р		-	-	0.56		
Junction to case, both leg conducting	R <sub>thJC</sub>		-	-	0.28	°C/W	
Case to heatsink	R <sub>thCS</sub>	Flat, greased surface	-	0.075	-		
Weight			-	30	-	g	
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)	
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)	
Case style					OT-227		



# VS-UFB201FA40

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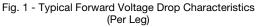


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

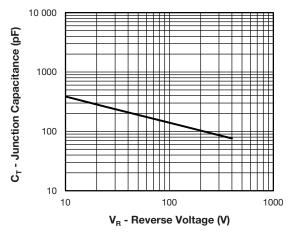


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

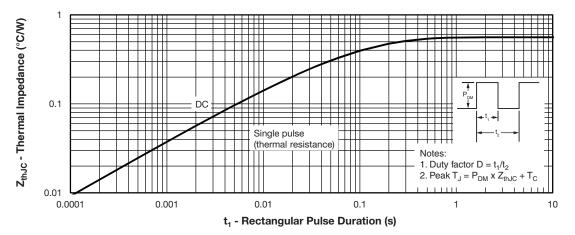


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics (Per Leg)

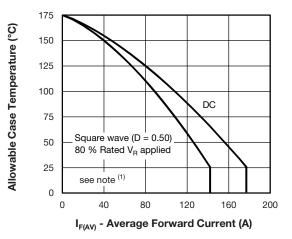
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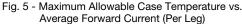
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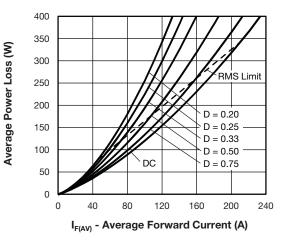


Fig. 6 - Forward Power Loss Characteristics (Per Leg)

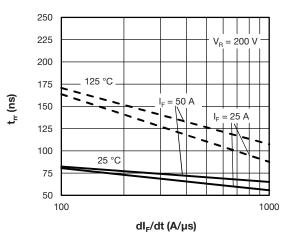
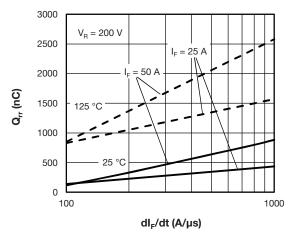


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt





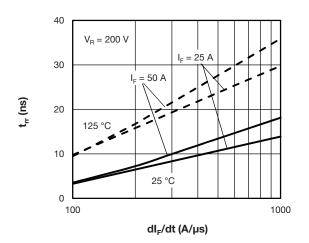


Fig. 9 - Typical Reverse Recovery vs. dl<sub>F</sub>/dt

#### Note

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ \mathsf{x} \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$ 

Revision: 10-Sep-2019

4

Document Number: 93793

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<sup>&</sup>lt;sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;



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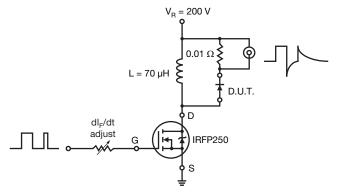
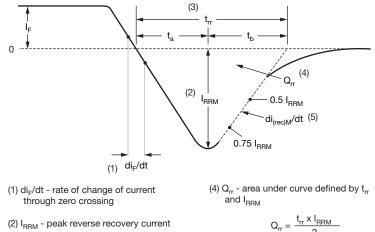
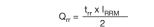


Fig. 10 - Reverse Recovery Parameter Test Circuit



(3)  $\mathrm{t}_{\mathrm{rr}}$  - reverse recovery time measured from zero crossing point of negative going  ${\rm I}_{\rm F}$  to point where a line passing through 0.75  $I_{\text{RRM}}$  and 0.50  $I_{\text{RRM}}$  extrapolated to zero current.



(5)  $di_{(rec)M}/dt$  - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 11 - Reverse Recovery Waveform and Definitions





### **ORDERING INFORMATION TABLE**

**Device code** 

e	vs-	UF	в	201	F	Α	40			
	1	2	3	4	5	6	(7)			
	1 - Vishay Semiconductors product									
	2 · 3 ·		Ultrafast rectifier Ultrafast Pt diffused							
	4		Current rating (201 = 200 A)							
	5	- Circ	Circuit configuration (two separate diodes, parallel pin-out)							
	6	- Pac	Package indicator (SOT-227 standard insulated base)							

7 Voltage rating (40 = 400 V)

CIRCUIT CONFIGURATION					
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING			
Two separate diodes, parallel pin-out	F	Lead Assignment			

LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95423						
Packaging information	www.vishay.com/doc?95425					

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SOT-227 Generation 2

#### **DIMENSIONS** in millimeters (inches)



#### Note

• Controlling dimension: millimeter



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